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(37 CFR 1.98(b))

APPLICANT
Toshiharu Furukawa et al.FILING DATE
October 4, 2004GROUP
2823

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	C.A.						
	C.B.						
	C.C.						
	C.D.						
	C.E.						
	C.F.						
	C.G.						
	C.H.						
	C.I.						
	C.J.						
	C.K.						

FOREIGN PATENTS OR PUBLISHED FOREIGN PATENT APPLICATIONS

		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION (YES/NO)
	C.L.						
	C.M.						
	C.N.						
	C.O.						
	C.P.						
	C.Q.						

OTHER DOCUMENTS (Including Author, Title, Date, Place of Publication)

JS	C.R.	C-H. Kiang, "Growth of Larger-Diameter Single-Walled Carbon Nanotubes," J. Phys. Chem. A 2000, 104, 2454-2456
JS	C.S.	E. Pfoenies, et al, "Single-Walled Carbon Nanotube Synthesis in CO Laser Pumped Monoxide Plasma", Oct 10, 2001
JS	C.T.	Y. Mo, et al, "The growth mechanism of carbon nanotubes from thermal cracking of acetylene over nickel catalyst supported on alumina," 2001 Elsevier Science B.V

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JS	I.R.	Z.Huang.; Z.F.Ren., "Growth of highly oriented carbon nanotubes by plasma-enhanced hot filament chemical vapor deposition." <u>Applied Physics Letters</u> , Vol 73, Number 26, 28 December 1998
↓	I.S.	G.S. Duesberg et al., <u>Large-Scale Integration of Carbon Nanotubes Into Silicon Based Microelectronics</u> , Proceedings of the SPIE, Bellingham, VA, Vol. 5118, May 21, 2003
JS	I.T.	Furukawa et al., <u>United States Patent Application Publication No. US 2005/0167655</u> , Publication Date: August 4, 2005

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J.R.	Z.F. Ren, et al, "Synthesis of Large Arrays of Well-Aligned Carbon Nanotubes on Glass", Science, Vol 282, 6 November 1998, 1105-1107
J.S.	Won Bong Choi, et al, "Ultrahigh density nanotransistors by using selectively grown vertical carbon nanotubes", Applied Physics Letters, Volume 79, Number 22, 26 November 2001
J.T.	Bo Zheng, et al, "Efficient CVD Growth of Single-Walled Carbon Nanotubes on Surfaces Using Carbon Monoxide Precursor", Nano Letters, xxxx Vol.0, No 0 A-D, American Chemical Society revised June 26, 2002

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